# HERAF1601G – HERAF1606G



# 16A, 50V - 600V High Efficient Rectifier

#### FEATURES

TAIWAN

• AEC-Q101 qualified available

SEMICONDUCTOR

- Glass passivated chip junction
- High efficiency, Low  $V_{\text{F}}$
- High current capability
- High reliability
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### **APPLICATIONS**

- DC to DC converter
- Switching mode converters and inverters
- Freewheeling application

### **MECHANICAL DATA**

- Case: ITO-220AC
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.70g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I <sub>F</sub>	16	А
V <sub>RRM</sub>	50 - 600	V
I <sub>FSM</sub>	250	А
T <sub>J MAX</sub>	150	°C
Package	ITO-220AC	
Configuration	Single	die





PIN 2 O-

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)								
PARAMETER	SYMBOL	HERAF	HERAF		HERAF	HERAF	HERAF	UNIT
		1601G	1602G	1603G	1604G	1605G	1606G	_
Marking code on the device		HERAF 1601G	HERAF 1602G	HERAF 1603G	HERAF 1604G	HERAF 1605G	HERAF 1606G	
Repetitive peak reverse voltage	$V_{RRM}$	50	100	200	300	400	600	V
Reverse voltage, total rms value	$V_{R(RMS)}$	35	70	140	210	280	420	V
Forward current	١ <sub>F</sub>			1	6			Α
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>			2	50			A
Junction temperature	TJ	-55 to +150		°C				
Storage temperature	T <sub>STG</sub>			-55 to	+150			°C



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THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case resistance	R <sub>eJC</sub>	2	°C/W

ELECTRICAL SPEC	IFICATIONS	(T <sub>A</sub> = 25°C unless othe	rwise noted)			
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward voltage <sup>(1)</sup>	HERAF1601G HERAF1602G HERAF1603G HERAF1604G	I <sub>F</sub> = 16A, T <sub>J</sub> = 25°C	V <sub>F</sub>	-	1.0	V
	HERAF1605G			-	1.3	V
	HERAF1606G			-	1.7	V
Reverse current @ rated V <sub>R</sub> <sup>(2)</sup>		$T_J = 25^{\circ}C$	I <sub>R</sub>	-	10	μA
		T <sub>J</sub> = 125°C		-	400	μA
Junction capacitance	HERAF1601G HERAF1602G HERAF1603G HERAF1604G HERAF1605G	1MHz, V <sub>R</sub> = 4.0V	CJ	150	-	pF
	HERAF1606G			110	-	pF
Reverse recovery time	HERAF1601G HERAF1602G HERAF1603G HERAF1604G HERAF1605G	IF = 0.5A, IR = 1.0A Irr = 0.25A	t <sub>rr</sub>	-	50	ns
	HERAF1606G			-	80	ns

#### Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING
HERAF16xG	ITO-220AC	50 / Tube
HERAF16xGH	ITO-220AC	50 / Tube

Notes:

1. "x" defines voltage from 50V(HERAF1601G) to 600V(HERAF1606G)

2. "H" means AEC-Q101 qualified



## HERAF1601G – HERAF1606G

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#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

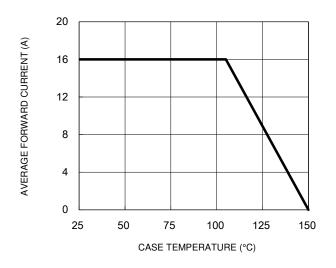
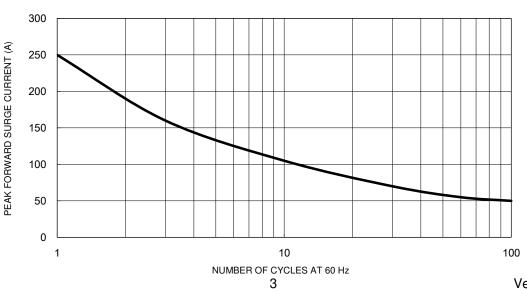


Fig.1 Forward Current Derating Curve

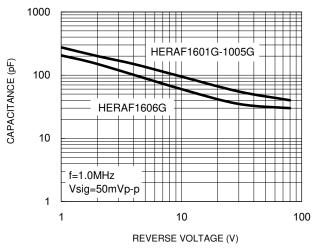
#### **Fig.3 Typical Reverse Characteristics**

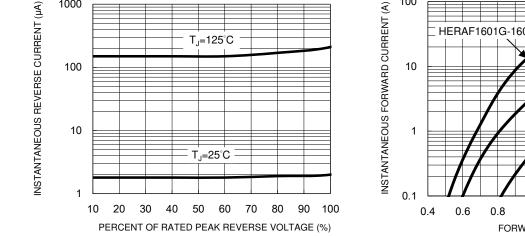
#### 100 1000 INSTANTANEOUS FORWARD CURRENT (A) HERAF1601G-1604G T\_=125°C 100 10 HERAF1605G 10 1 HERAF1606G T,=25°C Pulse width 300µs 1% duty cycle 1 0.1 20 10 30 40 50 60 70 80 90 100 0.4 0.6 0.8 1 1.2 1.4 1.6 1.8 FORWARD VOLTAGE (V)



#### Fig.5 Maximum Non-Repetitive Forward Surge Current

**Fig.4 Typical Forward Characteristics** 





**Fig.2 Typical Junction Capacitance** 



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#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

#### 50Ω 10Ω trr 🗕 NONINDUCTIVE NONINDUCTIVE w ~~~ +0.5A (-) ± DUT • (+) 50Vdc PULSE 0 GENERATOR (approx) -0.25A (NOTE 2) (-) 1Ω OSCILLOSCOPE 6 (+) (NOTE 1) -1.0A NOTES: 1. Rise Time=7ns max. Input Impedance= 圭 1 megohm 22pf 2. Rise Time=10ns max. Sourse Impedance= 50 ohms

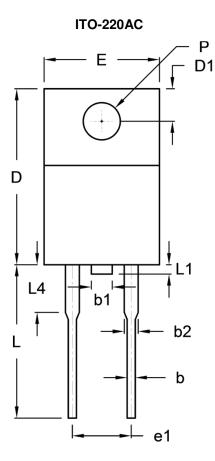
#### Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram

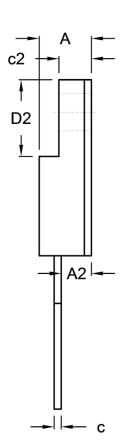


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### PACKAGE OUTLINE DIMENSIONS





DIM.	Unit (mm)		Unit	(inch)	
DIN.	Min.	Max.	Min.	Max.	
А	4.30	4.70	0.169	0.185	
A2	2.30	2.90	0.091	0.114	
b	0.50	0.90	0.020	0.035	
b1	-	1.80	-	0.071	
b2	0.95	1.45	0.037	0.057	
с	0.46	0.76	0.018	0.030	
c2	2.50	3.10	0.098	0.114	
D	14.80	15.50	0.583	0.610	
D1	2.40	3.20	0.094	0.126	
D2	6.30	6.90	0.248	0.272	
Е	9.60	10.30	0.378	0.406	
e1	4.95	5.20	0.195	0.205	
L	12.60	13.80	0.496	0.543	
L1	0.00	1.60	0.000	0.063	
L4	-	4.10	-	0.161	
Р	3.00	3.40	0.118	0.134	

#### **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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